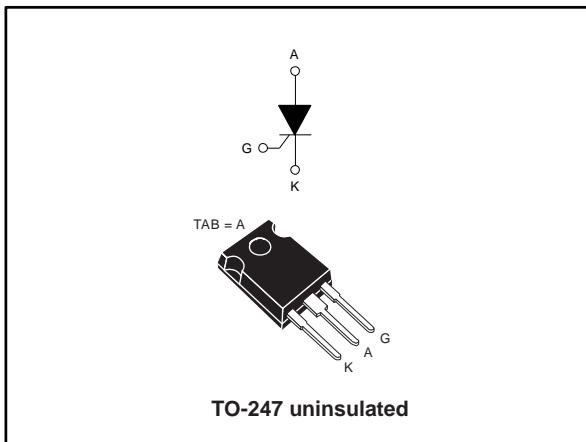


## 80 A high temperature Thyristor (SCR)

Datasheet - production data



### Features

- High junction temperature:  $T_j = 150^\circ\text{C}$
- Blocking voltage:  $V_{DRM} = V_{RRM} = 800 \text{ V}$
- Nominal current:  $I_{T(\text{RMS})} = 80 \text{ A}$
- Gate triggering current:  $I_{GT} \text{ max.} = 50 \text{ mA}$
- High noise immunity:  $dV/dt > 1 \text{ kV}/\mu\text{s}$
- Through hole package TO-247
- Ecopack®2 (includes halogen free & RoHS compliance)
- Increase of thermal margin due to extended  $T_j$  up to  $150^\circ\text{C}$
- Low  $I_D$  and  $I_R$  in blocking state

### Applications

- Solid state switch
- Battery charging system
- Variable speed motor drive
- Industrial welding systems
- AC-DC rectifier controlled bridge
- Soft starter systems

### Description

Available in high power package (TO-247), the device is suitable in applications where power switching ( $I_{T(\text{RMS})} = 80 \text{ A}$  at  $T_c = 126^\circ\text{C}$ ) and power dissipation ( $V_{TM} = 1.55 \text{ V}$  at  $160 \text{ A}$ ) are critical, such as motorbike voltage regulator, bypass AC switch, controlled rectifier bridge, solid state relay, battery charger, welding equipment and motor driver applications. The TM8050H-8W is available in through hole TO-247 package.

Table 1: Device summary

Symbol	Value
$I_{T(\text{RMS})}$	80 A
$V_{DRM}/V_{RRM}$	800 V
$I_{GT}$	50 mA
$T_j$	150 °C

# 1 Characteristics

Table 2: Absolute ratings (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)	$T_C = 126^\circ\text{C}$	$t_p = 8.3 \mu\text{s}$	80	A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)			50	A
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 10 \mu\text{s}$	$T_j \text{ initial} = 25^\circ\text{C}$	731	A
				670	
$I^2t$	$I^2t$ value for fusing		$T_j = 25^\circ\text{C}$	2245	$\text{A}^2\text{s}$
$V_{RRM} / V_{DRM}$	Maximum repetitive symmetric blocking voltage			800	V
$dI/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}, t_r \leq 100 \text{ ns}$	$f = 50 \text{ Hz}$	$T_j = 25^\circ\text{C}$	200	$\text{A}/\mu\text{s}$
$I_{GM}$	Peak gate current	$t_p = 20 \mu\text{s}$	$T_j = 150^\circ\text{C}$	8	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 150^\circ\text{C}$	1	W
$V_{RGM}$	Maximum peak reverse gate voltage			5	V
$T_{stg}$	Storage junction temperature range			-40 to +150	$^\circ\text{C}$
$T_j$	Maximum operating junction temperature			-40 to +150	$^\circ\text{C}$

Table 3: Electrical characteristics ( $T_j = 25^\circ\text{C}$  unless otherwise specified)

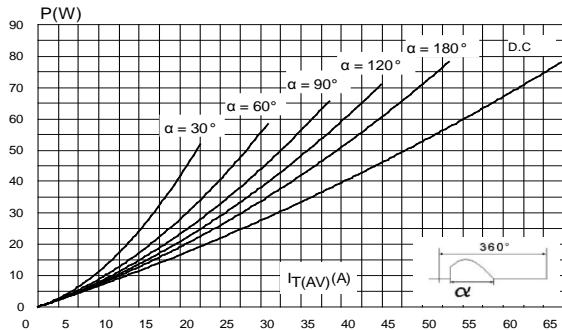
Symbol	Test Conditions	Value	Unit
$I_{GT}$	$V_D = 12 \text{ V}, R_L = 33 \Omega$	Min.	2.5
		Max.	50
$V_{GT}$	$V_D = 12 \text{ V}, R_L = 33 \Omega$	Max.	1.5
$V_{GD}$	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$	$T_j = 150^\circ\text{C}$	Min.
$I_H$	$I_T = 500 \text{ mA}, \text{gate open}$	Max.	100
$I_L$	$I_G = 1.2 \times I_{GT}$	Max.	125
$t_{gt}$	$I_T = 80 \text{ A}, V_D = V_{DRM}, I_G = 200 \text{ mA}, dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	Typ.	3
$dV/dt$	$V_D = 67\% V_{DRM}, \text{gate open}$	$T_j = 150^\circ\text{C}$	Min.
$t_q$	$I_T = 33 \text{ A}, dI_T/dt = 10 \text{ A}/\mu\text{s}, V_R = 75 \text{ V}, V_D = 400 \text{ V}, dV_D/dt = 20 \text{ V}/\mu\text{s}, t_p = 100 \mu\text{s}$	$T_j = 150^\circ\text{C}$	Max.
			150
$V_{TM}$	$I_{TM} = 160 \text{ A}, t_p = 380 \mu\text{s}$	$T_j = 25^\circ\text{C}$	Max.
$V_{TO}$	Threshold voltage	$T_j = 150^\circ\text{C}$	Max.
$R_D$	Dynamic resistance	$T_j = 150^\circ\text{C}$	Max.
$I_{DRM}$	$V_D = V_{DRM} = V_R = V_{RRM} = 800 \text{ V}$	$T_j = 25^\circ\text{C}$	Max.
$I_{RRM}$		$T_j = 150^\circ\text{C}$	Max.

**Table 4: Thermal parameters**

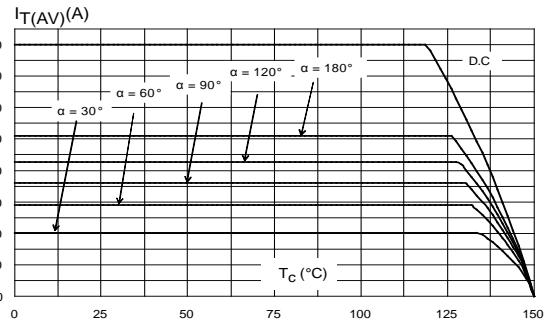
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (DC,max.)	0.30	°C/W
$R_{th(j-a)}$	Junction to ambient (DC, typ., $S_{cu} = 2.1 \text{ cm}^2$ )	50	

## 1.1 Characteristics (curves)

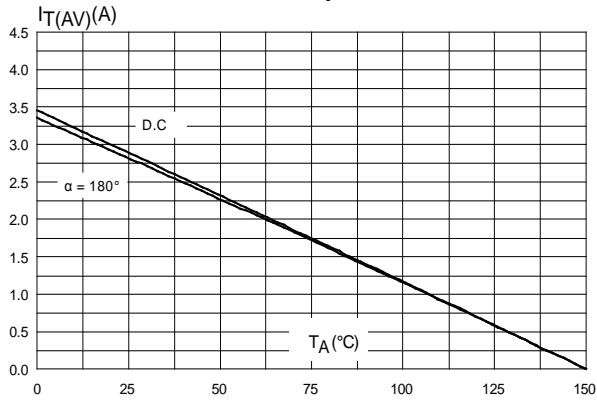
**Figure 1: Maximum average power dissipation versus average on-state current**



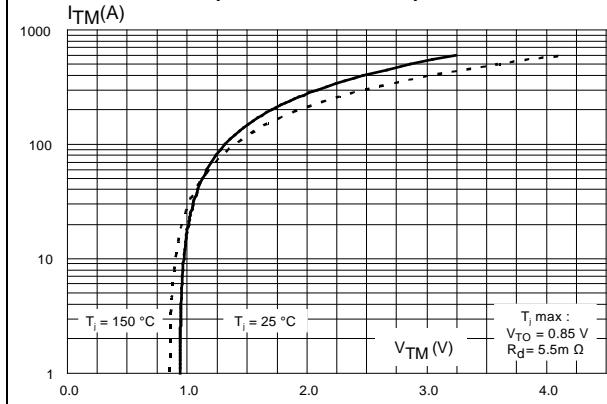
**Figure 2: Average and DC on-state current versus case temperature**



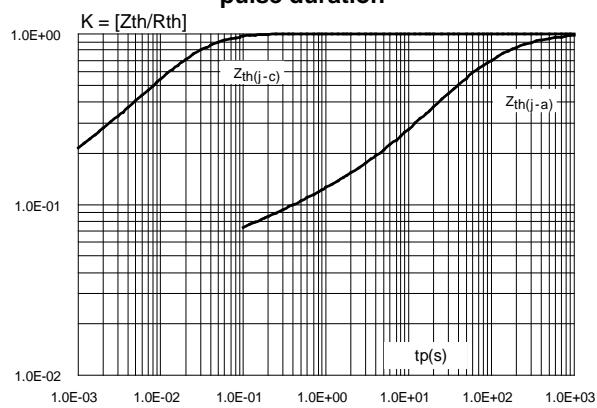
**Figure 3: Average and D.C. on state current versus ambient temperature**



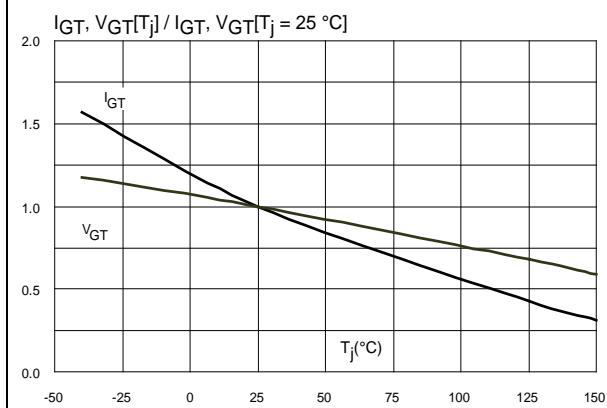
**Figure 4: On-state characteristics (maximum values)**



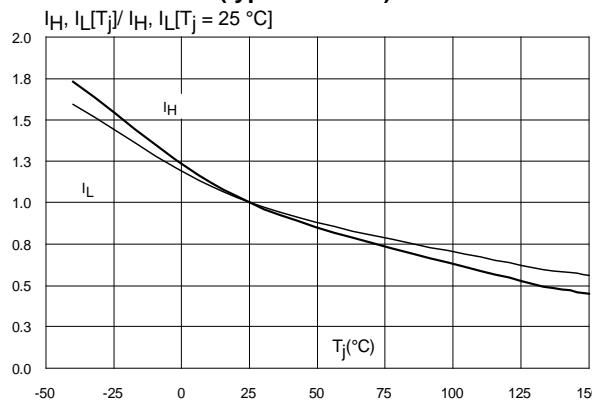
**Figure 5: Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration**



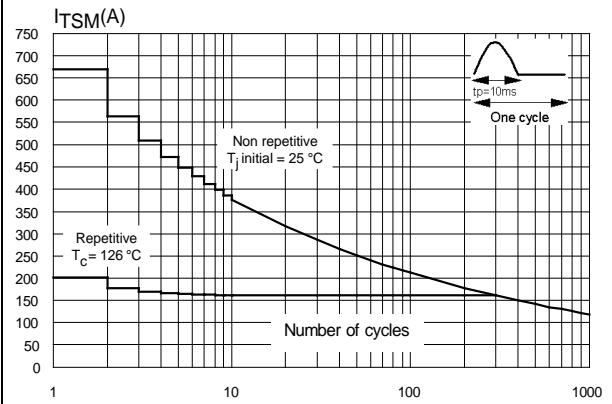
**Figure 6: Relative variation of gate trigger current and gate voltage versus junction temperature**



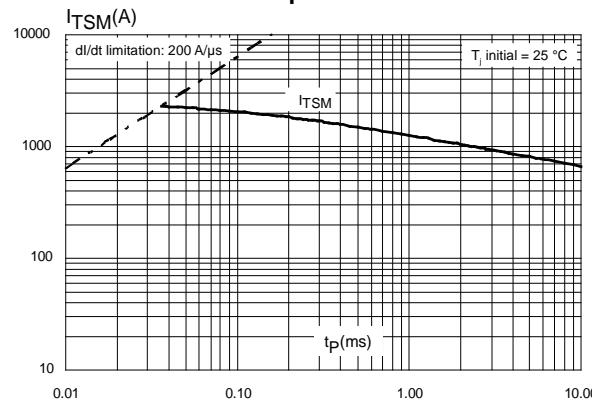
**Figure 7: Relative variation of holding current and latching current versus junction temperature (typical values)**



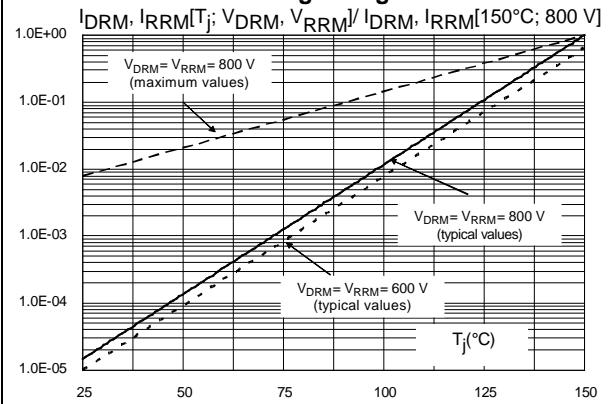
**Figure 8: Surge peak on state current versus number of cycles**



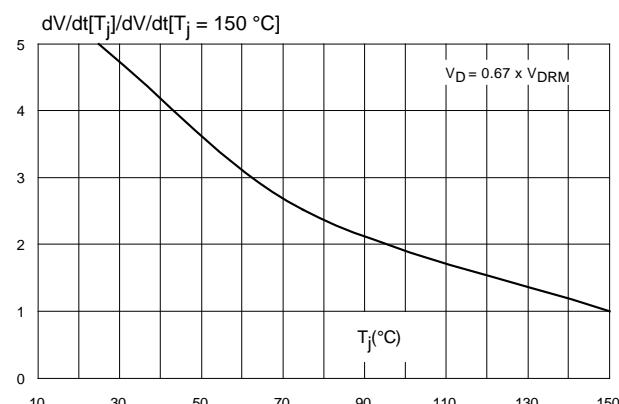
**Figure 9: Non repetitive surge peak on state current for a half cycle sine pulse versus pulse width t<sub>p</sub> < 10 ms**



**Figure 10: Relative variation of leakage current versus junction temperature for different values of blocking voltage**



**Figure 11: Relative variation of static dV/dt immunity versus junction temperature (typical values)**



## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free package lead finishing; halogen-free moulding resin

### 2.1 TO-247 package information

Figure 12: TO-247 package outline

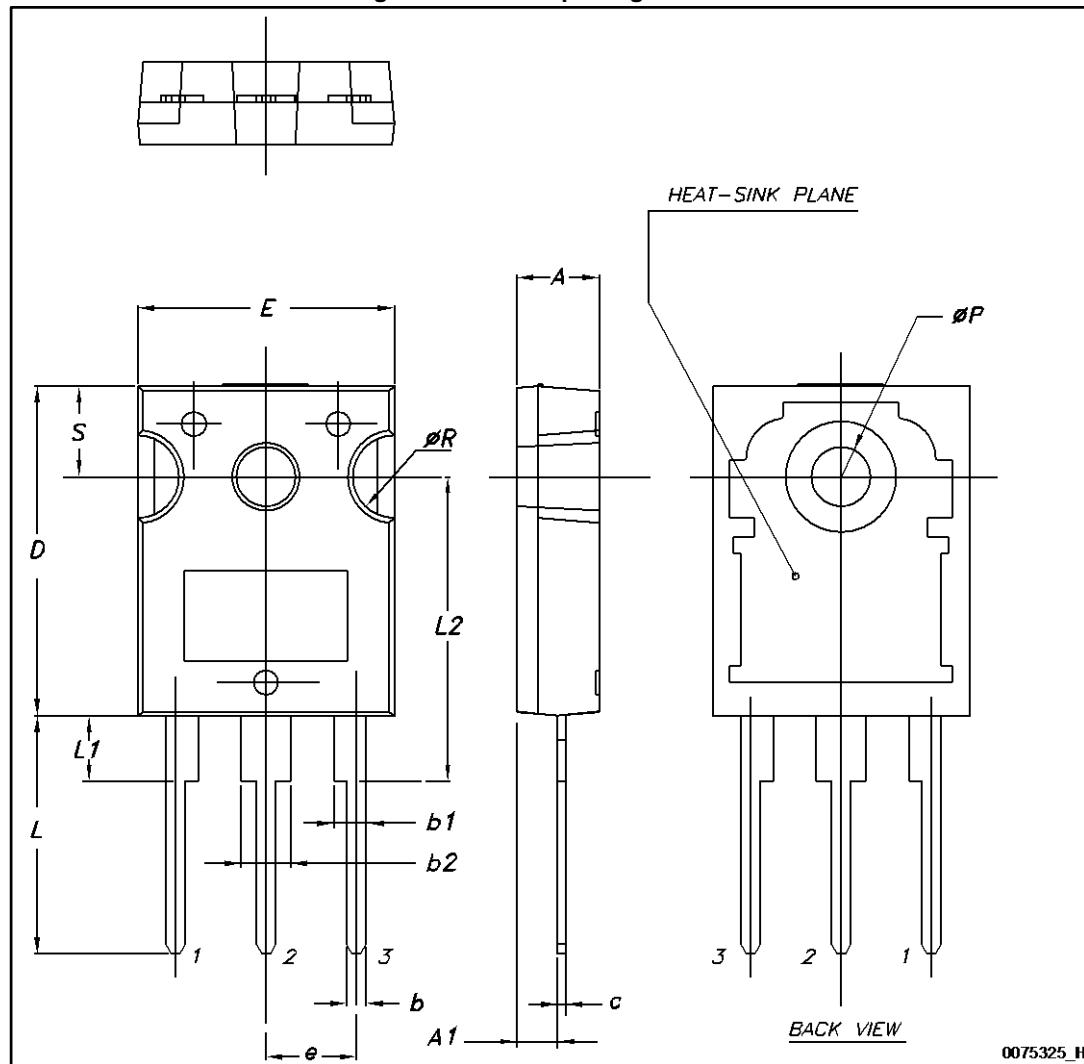


Table 5: TO-247 package mechanical data

Dim.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.1909		0.2028
A1	2.20		2.60	0.0866		0.1024
b	1.0		1.40	0.0394		0.0551
b1	2.0		2.40	0.0787		0.0945
b2	3.0		3.40	0.1181		0.1339
c	0.40		0.80	0.0157		0.0315
D <sup>(2)</sup>	19.85		20.15	0.7815		0.7933
E	15.45		15.75	0.6083		0.6201
e	5.30	5.45	5.60	0.2087	0.2146	0.2205
L	14.20		14.80	0.5591		0.5827
L1	3.70		4.30	0.1457		0.1693
L2		18.50			0.7283	
ØP <sup>(3)</sup>	3.55		3.65	0.1398		0.1437
ØR	4.50		5.50	0.1772		0.2165
S	5.30	5.50	5.70	0.2087	0.2165	0.2244

**Notes:**

(1)Inch dimensions given only for reference

(2)Dimension D plus gate protrusion does not exceed 20.5 mm

(3)Resin thickness around the mounting hole is not less than 0.9 mm

### 3 Ordering information

Figure 13: Ordering information scheme

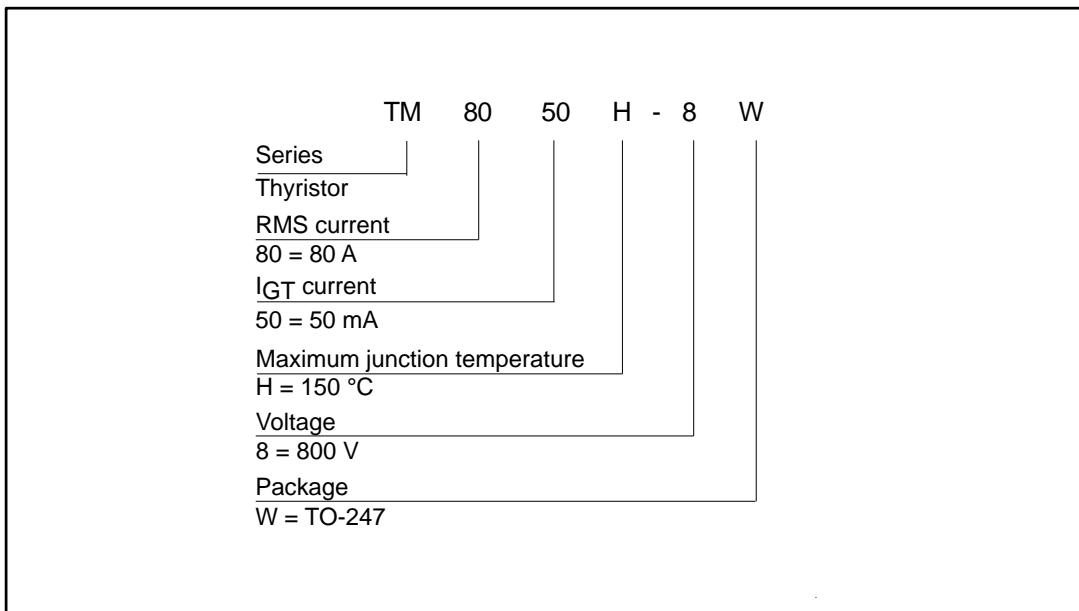


Table 6: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TM8050H-8W	TM8050H8	TO-247	4.43 g	30	Tube

### 4 Revision history

Table 7: Document revision history

Date	Revision	Changes
03-May-2016	1	Initial release.

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